TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74LCX652FS

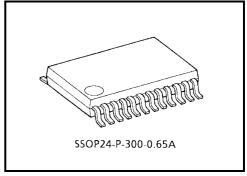
Low-Voltage Octal Bus Transceiver/Register with 5-V Tolerant Inputs and Outputs

The TC74LCX652FS is a high-performance CMOS octal bus transceiver/register. Designed for use in 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

This device is designed for low-voltage (3.3 V) VCC applications, but it could be used to interface to 5-V supply environment for both inputs and outputs.

This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.14 g (typ.)

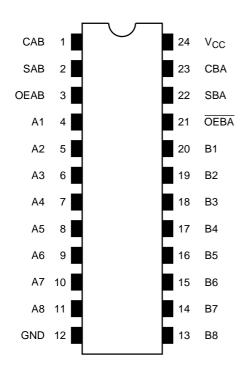
Features

- Low-voltage operation: V_{CC} = 2.0 to 3.6 V
- High-speed operation: $t_{pd} = 7.0 \text{ ns (max) (VCC} = 3.0 \text{ to } 3.6 \text{ V)}$
- Output current: $|I_{OH}|/I_{OL} = 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$
- Latch-up performance: ±500 mA
- Available in SSOP
- Bidirectional interface between 5 V and 3.3 V signals
- Power-down protection provided on all inputs and outputs
- Pin and function compatible with the 74 series (74AC/F/ALS/LS etc.) 652 type

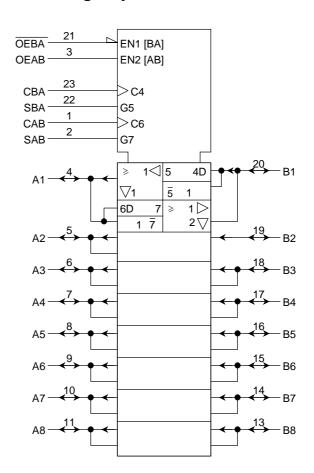
Note 1: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input levels fixed by means of pull-up or pull-down resistors.

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

		Contro	I Inputs			В	us	Function								
OEAB	OEBA	CAB	CBA	SAB	SBA	Α	В	Function								
		X*	X*	Х	Х	Input	Input	The output functions of A and B busses are								
		*	^.	^	^	Z Z		disabled.								
L	Н	\		Х	Х	Х	Х	Both A and B busses are used as inputs to the internal flip-flops. Data on the bus will be stored on the rising edge of the Clock.								
						Input	Output									
		X*	X*	L	X	L	L	The data on the A bus are displayed on the B bus.								
						Н	Н									
		↑	X*	L	X	L	L	The data on the A bus are displayed on the								
н	Н		^*	L	^	н	Н	B bus, and are stored into the A storage flip-flops on the rising edge of CAB.								
		X*	X*	Н	Х	х	Qn	The data in the A storage flop-flops are displayed on the B bus.								
		_							L	L	The data on the A bus are stored into the A					
		_	X*	Н	Х	Н	Н	storage flip-flops on the rising edge of CAB, and the stored data propagate directly onto the B bus.								
					L	L	L	L	L	L	L	L		Output	Input	
		X*	X*	X									L	L	The data on the B bus are displayed on the A bus.	
						Н	Н									
		X*	_	Х		L	L The data on the B by	The data on the B bus are displayed on the								
L	L	Α**		^	L	Н	Н	A bus, and are stored into the B storage flip-flops on the rising edge of CBA.								
		X*	X*	Х	Н	Qn	Х	The data in the B storage flip-flops are displayed on the A bus.								
			↑			L	L	The data on the B bus are stored into the B								
		X*		X	Н	н	н	storage flip-flops on the rising edge of CBA, and the stored data propagate directly onto the A bus.								
						Output	Output									
н	L	X*	X*	н	н	Qn	Qn	The data in the A storage flop-flops are displayed on the B bus, and the data in the B storage flop-flops are displayed on the A.								

X: Don't care

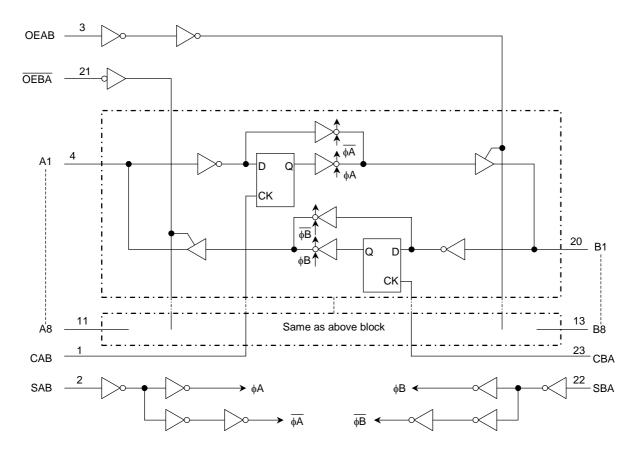
Z: High impedance

Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

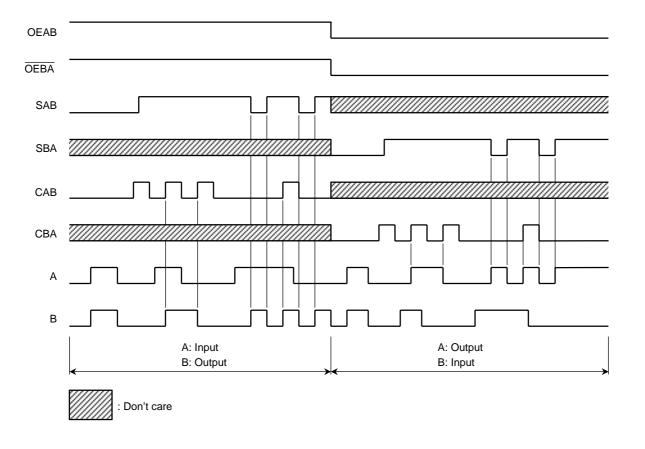
*: The clocks are not internally gated with either OEAB or $\overline{\text{OEBA}}$.

Therefore, data on the A and/or B busses may be clocked into the storage flip-flops at any time.

System Diagram



Timing Chart





Maximum Ratings

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	−0.5 to 7.0	V	
DC input voltage (CAB, CBA, SAB, SBA, OEAB, OEBA)	V _{IN}	-0.5 to 7.0	V	
		-0.5 to 7.0 (Note 2)		
DC bus I/O voltage	V _{I/O}	-0.5 to V _{CC} + 0.5	V	
		(Note 3)		
Input diode current	I _{IK}	-50	mA	
Output diode current	lok	±50 (Note 4)	mA	
DC output current	lout	±50	mA	
Power dissipation	P_{D}	180	mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65 to 150	°C	

Note 2: Output in OFF state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V	2.0 to 3.6	V	
Fower supply voltage	V _{CC}	1.5 to 3.6 (Note 5)	V	
Input voltage (CAB, CBA, SAB, SBA, OEAB, OEBA)	V _{IN}	0 to 5.5	V	
Bus I/O voltage	V	0 to 5.5 (Note 6)	V	
Bus I/O Voltage	V _{I/O}	0 to V _{CC} (Note 7)	V	
Output current	la/la.	±24 (Note 8)	mA	
Output current	I _{OH} /I _{OL}	±12 (Note 9)	ША	
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 10)	ns/V	

Note 5: Data retention only

Note 6: Output in OFF state

Note 7: High or low state

Note 8: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 9: $V_{CC} = 2.7 \text{ to } 3.0 \text{ V}$

Note 10: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

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TC74LCX652FS



Electrical Characteristics

DC Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Characteristics		Symbol	Test Condition			Min	Max	Unit
					V _{CC} (V)			
Input voltage	H-level	V _{IH}	_		2.7 to 3.6	2.0	—	V
input voltage	L-level	V _{IL}	_		2.7 to 3.6		0.8	V
		V _{OH}		$I_{OH} = -100 \ \mu A$	2.7 to 3.6	V _{CC} - 0.2	_	V
	H-level		V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -12 \text{ mA}$	2.7	2.2		
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	
	I lavel		$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	2.7 to 3.6	_	0.2	
				I _{OL} = 12 mA	2.7	_	0.4	
	L-level	VoL		I _{OL} = 16 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage current		I _{IN}	V _{IN} = 0 to 5.5 V		2.7 to 3.6	_	±5.0	μΑ
2 state sutput OFF sta	to ourront	1	$V_{IN} = V_{IH}$ or V_{IL}		0.74-0.0		.5.0	
3-state output OFF state current		loz	V _{OUT} = 0 to 5.5 V		2.7 to 3.6	_	±5.0	μА
Power-off leakage current		I _{OFF}	V _{IN} /V _{OUT} = 5.5 V		0	_	10.0	μА
Quiescent supply current		l	V _{IN} = V _{CC} or GND		2.7 to 3.6	_	10.0	
		I_{CC} $V_{IN}/V_{OUT} = 3.6 \text{ to } 5.5$		5 V	2.7 to 3.6	_	±10.0	μΑ
Increase in Icc per input		Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6	_	500	



AC Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Characteristics S		Test Condition		Min	Max	Unit
			V _{CC} (V)			
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.7	_	—	MHz
	max	3 , 3	3.3 ± 0.3	150		
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.7	_	8.0	ns
(An, Bn-Bn, An)	t _{pHL}	Figure 1, Figure 2	3.3 ± 0.3	1.5	7.0	
Propagation delay time	t _{pLH}	Figure 4 Figure 5	2.7	_	9.5	
(CAB, CBA-Bn, An)	t _{pHL}	Figure 1, Figure 5	3.3 ± 0.3	1.5	8.5	ns
Propagation delay time	t _{pLH}	F: 4 F: 0	2.7		9.5	
(SAB, SBA-Bn, An)	t _{pHL}	Figure 1, Figure 2	3.3 ± 0.3	1.5	8.5	ns
Output enable time	t _{pZL}	Figure 4 Figure 2 Figure 4	2.7	_	9.5	
(OEAB, OEBA -An, Bn)	r) Figure 1, Figure 3, Figure 4	3.3 ± 0.3	1.5	8.5	ns	
Output disable time	t _{pLZ}	Figure 1, Figure 3, Figure 4	2.7	_	9.5	ns
(OEAB, OEBA -An, Bn)	t _{pHZ}		3.3 ± 0.3	1.5	8.5	
Minimum nula a width	t _W (H)	Figure 1, Figure 5	2.7	3.3	_	- ns
Minimum pulse width	t _W (L)		3.3 ± 0.3	3.3	_	
Minimum setup time	4	Figure 4 Figure 5	2.7	2.5	_	
Minimum setup time	t _s	Figure 1, Figure 5	3.3 ± 0.3	2.5	_	ns
Minimum hold time	4.	E. 1 E. E	2.7	1.5	_	20
Minimum noid time	th	Figure 1, Figure 5	3.3 ± 0.3	1.5	_	ns
Output to output alrays	t _{osLH}	(Note 11)	2.7	_	_	20
Output to output skew	t _{osHL}		3.3 ± 0.3	_	1.0	ns

Note 11: Parameter guaranteed by design. $(t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|)$

Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.5 \text{ ns}$, $C_L = 50 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 1	2) 3.3	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 1)	2) 3.3	0.8	V

Note 12: Characterized with 7 outputs switching from high-to-low or low-to- high. The remaining output is measured in the low state.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	OEAB, OEBA, CAB, CBA, SAB, SBA		3.3	7	pF
Bus input capacitance	C _{I/O}	An, Bn		3.3	8	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note 13)	3.3	25	pF

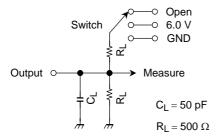
Note 13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch
t _{pLH} , t _{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V
t _{pHZ} , t _{pZH}	GND
t _w , t _s , t _h , f _{max}	Open

Figure 1

AC Waveform

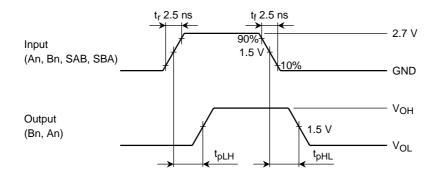
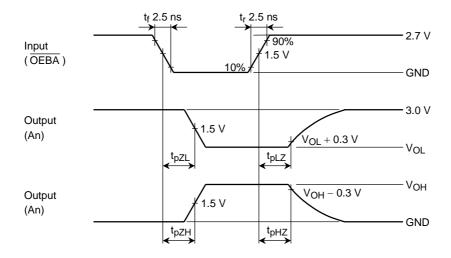


Figure 2 t_{pLH}, t_{pHL}



 $Figure \ 3 \quad t_{pLZ}, \, t_{pHZ}, \, t_{pZL}, \, t_{pZH}$

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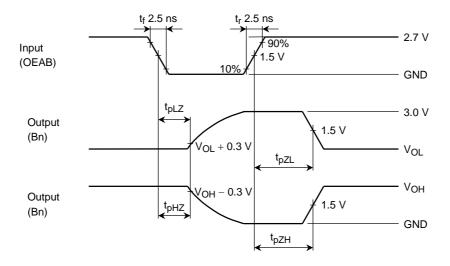
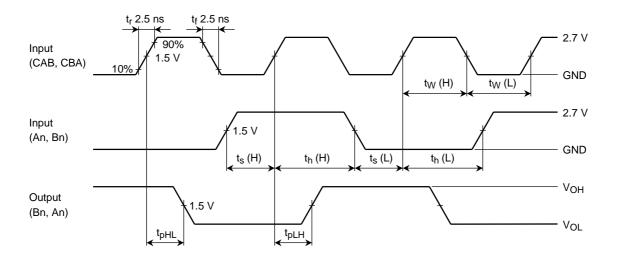


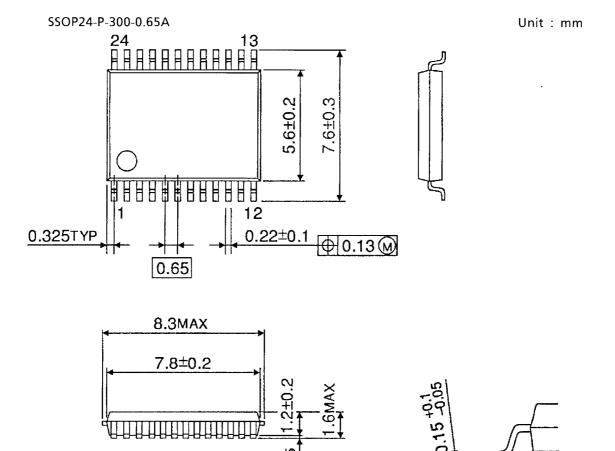
Figure 4 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$



 $\label{eq:figure 5} \textbf{Figure 5} \quad t_{pLH},\,t_{pHL},\,t_{w},\,t_{s},\,t_{h}$

0.45±0.2

Package Dimensions



Weight: 0.14 g (typ.)

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